Ordering number : ENN3702B

NPN Triple Diffused Planar Silicon Transistor

2SC4633LS

1200V / 30mA High-Voltage Amplifier, High-Voltage Switching Applications

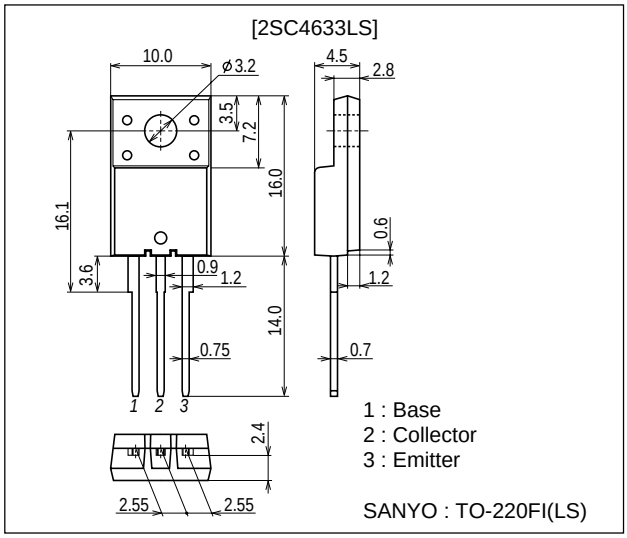
Features

- High breakdown voltage(V_{CEO} min=1200V).
- Small Cob(typical Cob=2.0pF).
- Full-isolation package.
- High reliability(Adoption of HVP process).

Package Dimensions

unit : mm

2079D



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		1500	V
Collector-to-Emitter Voltage	V_{CEO}		1200	V
Emitter-to-Base Voltage	V_{EBO}		5	V
Collector Current	I_C		30	mA
Collector Current (Pulse)	I_{CP}		100	mA
Collector Dissipation	P_C		2	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=1200V, I_E=0			1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0			1	μA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=1.5mA	10		60	
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=1.5mA		6		MHz

Continued on next page.

SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Continued from preceding page.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=3mA, I_B=0.6mA			5	V
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=3mA, I_B=0.6mA			2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	1500			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	1200			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Output Capacitance	Cob	V_{CB}=100V, f=1MHz		2.0		pF
Thermal Resistance	Rthj-c	Junction – case			8.3	°C / W